

INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT

MAY 24 2002

Sheet 1 of 3

FILING DATE: September 15, 2000

APPLICANT: Svetlana B. Radovanov et al.

GROUP ART UNIT: 2858 EXAMINER: Not Yet Assigned

## U.S. PATENT DOCUMENTS

Examiner's Initials#	Cite No.	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication or of issue of Cited Document MM-DD-YYYY
		Number	Kind Code		
2X	1A	4,021,675		Shifrin	05-03-1977
	2A	4,135,097		Formeris et al.	01-16-1979
	3A	4,228,358		Ryding	10-14-1980
	4A	4,234,797		Ryding	11-18-1980
	5A	4,361,762		Douglas	11-30-1982
	6A	4,421,988		Robertson et al.	12-20-1983
	7A	4,433,247		Turner	02-21-1984
	8A	4,463,255		Robertson et al.	07-31-1984
	9A	4,539,217		Farley	09-03-1985
	10A	4,587,433		Farley	05-06-1986
	11A	4,595,837		Wu et al.	06-17-1986
	12A	4,744,938		Ruddy	05-17-1988
	13A	4,751,393		Corey Jr. et al.	06-14-1988
	14A	4,764,394		Conrad	08-16-1988
	15A	4,786,814		Kolondra et al.	11-22-1988
	16A	4,937,205		Nakayama et al.	06-26-1990
	17A	5,015,493		Gruen	05-14-1991
	18A	5,126,163		Chan	06-30-1992
	19A	5,184,398		Moslehi	02-09-1993
	20A	5,206,180		Yoshida	04-27-1993
	21A	5,266,890		Kumbasar et al.	11-30-1993
	22A	5,286,676		Kruger et al.	02-15-1994
	23A	5,289,010		Shohet	02-22-1994
	24A	5,350,926		White et al.	09-27-1994
	25A	5,354,381		Sheng	10-11-1994
	26A	5,374,456		Matossian et al.	12-10-1994
	27A	5,452,177		Frutiger	09-19-1995
	28A	5,572,038		Sheng et al.	11-05-1996
	29A	5,653,811		Chan	08-05-1997
	30A	5,654,043		Shao et al.	08-05-1997
	31A	5,658,423		Angell et al.	08-19-1997
	32A	5,711,812		Chapek et al.	01-27-1998
	33A	5,728,253		Saito et al.	03-17-1998
	34A	5,814,823		Benveniste	09-29-1998
	35A	5,861,632		Rohner	01-19-1999

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36A	5,825,035	Mizumura et al.	10-20-1998
37A	5,883,391	Adibi et al.	03-16-1999
38A	5,911,832	Denholm et al.	06-15-1999
39A	6,020,592	Liebert et al.	02-01-2000
40A	6,028,324	Su et al.	02-22-2000
41A	6,050,218	Chen et al.	04-18-2000

## FOREIGN PATENT DOCUMENTS

Examiner's Initials#	Cite No.	Foreign Patent Document			Name of Patentee or Applicant of Cited Document (not necessary)	Date of Publication of Cited Document MM-DD-YYYY	Translation (Y/N)
		Office/Country	Number	Kind Code			
ST	42A	EP	0 532 283	B1	Sharp Kabushiki Kaisha	17.03.93	Y
ST	43A	EP	0 860 854	A1	Eaton Corporation	26.08.98	Y
ST	44A	EP	0 994 203	A2	Eaton Corporation	19.04.00	Y

## OTHER ART — NON PATENT LITERATURE DOCUMENTS

Examiner's Initials#	Cite No	Include name of the author (in CAPITAL LETTERS) title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, relevant page(s), volume-issue number(s), publisher, city and/or country where published.	Translation (Y/N)
ST	45A	BASRA, et al., "A Study of Wafer and Device Charging During High Current Ion Implantation", Varian Research Center, pp. 1-11	
	46A	EERNISSE, E.P., et al., "Ion Beam Profile Monitor," Rev. Sci. Instrum., vol. 46, No. 3 pp. 266-268 (Mar. 1975)	
	47A	FANG et al., "Evaluation of Different Wafer Charging Metrology Protocols for Thin Dielectrics", Varian Semiconductor Equipment Associates, Inc., pp. 1-4	
	48A	JAMBA, D.M., "Dosimetry Measurement In Ion Implanters," Nuclear Instruments and Methods 189, pp. 253-263, North Holland Publishing Company (1981)	
	49A	JAMBA, D.M., "Semiconductor Measurement Technology: Some Aspects of Dose Measurement for Accurate Ion Implantation," NBS Special Publication 400-39, pp. 1-36 (Issued Jul. 1977)	
	50A	JAMBA, D.M., "Secondary Particles Collection in Ion Implantation Dose Measurement," Rev. Sci. Instrum., vol. 49, No. 5, pp. 634-638 (May 1978)	
	51A	JONES, E.C. et al., "Plasma Doping Dosimetry," IEEE Trans. on Plasma Science, Vol. 25, No. 1, February, 1997	
	52A	KELLERMAN, P., "PIII Dosimetry," EATON, Implant Systems Division, April 1999, pp. 1-13	
	53A	KONDOW, E. et al., "In-Line Monitoring of HF-Last Cleaning of Implanted and Non-Implanted Silicon Surfaces by Non-Contact Surface Charge Measurements", <i>Electrochemical Society Proceedings</i> , Vol. 97-35, pp 221-228	
	54A	LUKASZEK, W. et al., "Charging Studies With Charm," <i>Nuclear Instruments and Methods in Physics Research</i> , pp 143-147 (1991)	
	55A	LUKASZEK, et al., "Measurement of Process Induced Wafer Potentials", <i>Ion Implant Technology—92</i> , pp. 645-650, (1993)	

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EXAMINER: Not Yet Assigned

<i>2f</i>	56A	MACK, M.E. et al., "Wafer Charging and Beam Interactions in Ion Implantation", <i>Nuclear Instruments and Methods in Physics Research</i> , pp 405-411 (1985)		
	57A	MCCARTHY, et al., "Applications of a New Wafer Surface Charge Monitor", EOS/ESD Symposium Proceedings, pp. 182-185 (1990)		
	58A	MCKENNA, C.M., "High Current Dosimetry Techniques," <i>Radiation Effects</i> , vol. 44, pp. 93-110 (1979)		
	59A	MEHTA, et al., "Charge Control in a Ribbon Beam High Current Ion Implanter", <i>Varian Ion Implant Systems</i> , pp. I-4		
	60A	MEHTA, et al., "Comparison of Positive and Negative Charging with CHARM-2 Wafers and Antenna Structures", <i>Varian Ion Implant Systems</i> , pp. 1-9		
	61A	SHAULY, E.N. et al., "In-Situ Control of Wafer Charge Neutralization During High Current Ion Implants", <i>Materials Research Society</i> , Vol. 316, pp 633-638 (1994)		
	62A	SINCLAIR et al., "Gate Oxides in High Current Implanters: how do they survive?", <i>Nuclear Instruments and Methods of Physics Research B55</i> , pp. 115-123 (1991)		
	63A	YOSHIDA, Y. et al., "Quantitative Monitoring of Charging-Up Employing EEPROM Device", pp 110-117		
	64A	Patent Abstract of Japan, Publication Number 10092886, Hitachi Ltd.		

EXAMINER

*Trung Nguyen*

DATE CONSIDERED

*11/15/02*

#EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

\*a copy of this reference is not provided as it was previously cited by or submitted to the office in a prior application, Serial No. \_\_\_\_\_, filed \_\_\_\_\_, and relied upon for an earlier filing date under 35 U.S.C. 120 (continuation, continuation-in-part, and divisional applications).

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